45 V, 1 A PNP medium power transistors Rev. 9 — 13 October 2011

1. **Product profile**

1.1 General description

PNP medium power transistor series in Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number ^[1]	Package	NPN complement		
	NXP	JEITA	JEDEC	
BCP51	SOT223	SC-73	-	BCP54
BCX51	SOT89	SC-62	TO-243	BCX54
BC51PA	SOT1061	-	-	BC54PA

[1] Valid for all available selection groups.

1.2 Features and benefits

- High current
- Three current gain selections
- High power dissipation capability
- Exposed heatsink for excellent thermal and electrical conductivity (SOT89, SOT1061)
- Leadless very small SMD plastic package with medium power capability (SOT1061)
- AEC-Q101 qualified

1.3 Applications

- Linear voltage regulators
- High-side switches
- Battery-driven devices
- Power management
- MOSFET drivers
- Amplifiers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-1	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-2	А



45 V, 1 A PNP medium power transistors

Table 2.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
h _{FE}	DC current gain	V _{CE} = –2 V; I _C = –150 mA	63	-	250	
	h _{FE} selection -10	V _{CE} = –2 V; I _C = –150 mA	63	-	160	
	h _{FE} selection -16	V _{CE} = –2 V; I _C = –150 mA	100	-	250	

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
SOT223			
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3 sym028
SOT89			
1	emitter		
2	collector		2
3	base		3 - 1 1 006aaa231
SOT1061			
1	base		
2	emitter	3	3
3	collector		1
		Transparent top view	

45 V, 1 A PNP medium power transistors

3. Ordering information

Table 4. Ordering information					
Type number ^[1]	Package				
	Name	Description	Version		
BCP51	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		
BCX51	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89		
BC51PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 \times 2 \times 0.65 mm	SOT1061		

[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes Type number Image: Code State Stat	Marking code
BCP51	BCP51
BCP51-10	BCP51/10
BCP51-16	BCP51/16
BCX51	AA
BCX51-10	AC
BCX51-16	AD
BC51PA	BP
BC51-10PA	BQ
BC51-16PA	BR

45 V, 1 A PNP medium power transistors

5. Limiting values

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter	-	-45	V
V _{CEO}	collector-emitter voltage	open base	-	-45	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-2	А
I _B	base current		-	-0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-0.3	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	BCP51		<u>[1]</u> _	0.65	W
			[2]	1.00	W
			[3]	1.35	W
	BCX51		[1] _	0.50	W
			[2] _	0.95	W
			[3]	1.35	W
	BC51PA		<u>[1]</u> _	0.42	W
			[2]	0.83	W
			[3]	1.10	W
			[4] _	0.81	W
			[5]	1.65	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

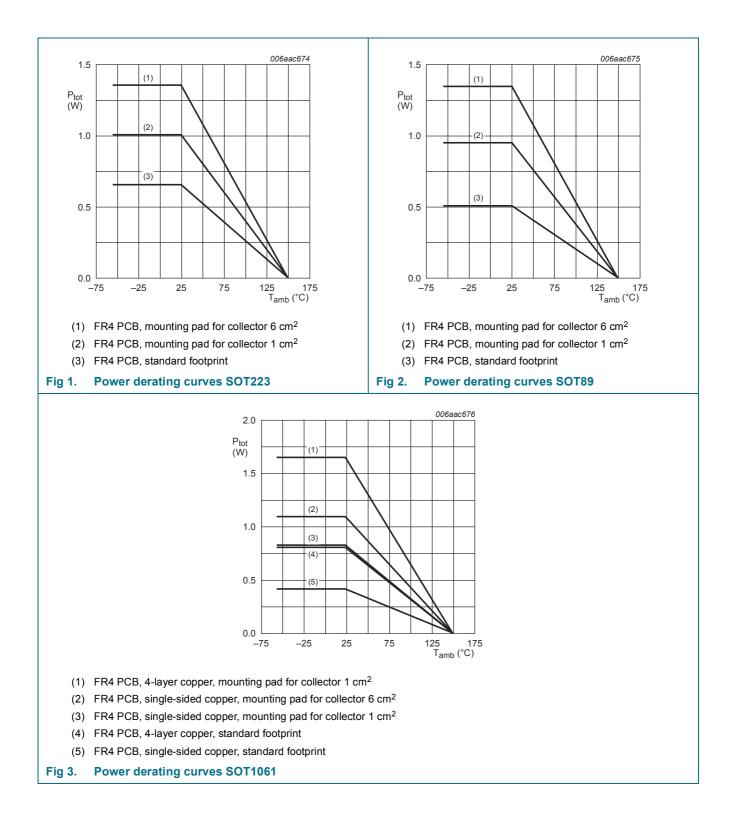
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

BCP51; BCX51; BC51PA

45 V, 1 A PNP medium power transistors



5 of 22

45 V, 1 A PNP medium power transistors

6. Thermal characteristics

Symbol	Parameter	Conditions	Ν	Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from	in free air			.76		•••••
	junction to ambient						
	BCP51		<u>[1]</u> _		-	192	K/W
			[2]		-	125	K/W
			[3] _		-	93	K/W
	BCX51		<u>[1]</u>		-	250	K/W
			[2] _		-	132	K/W
			[3]		-	93	K/W
	BC51PA		<u>[1]</u> _		-	298	K/W
			[2] _		-	151	K/W
			[3] _		-	114	K/W
			[4] _		-	154	K/W
			[5] _		-	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point						
	BCP51		-		-	16	K/W
	BCX51		-		-	16	K/W
	BC51PA		_		_	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

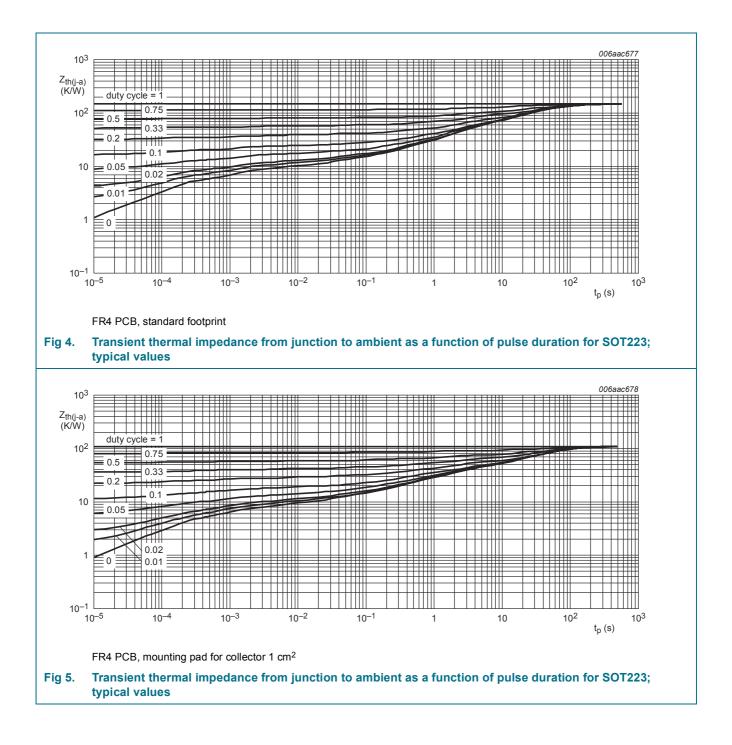
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

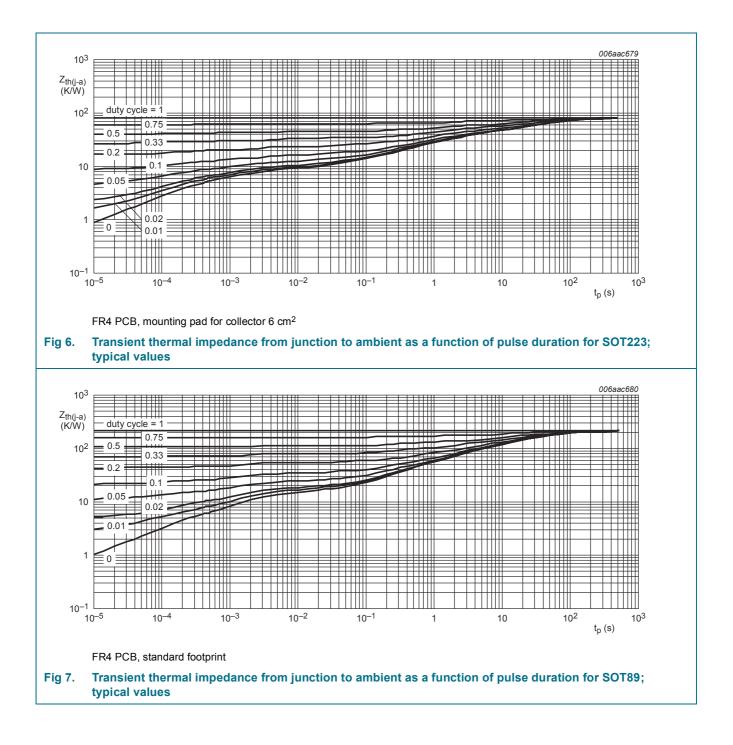
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

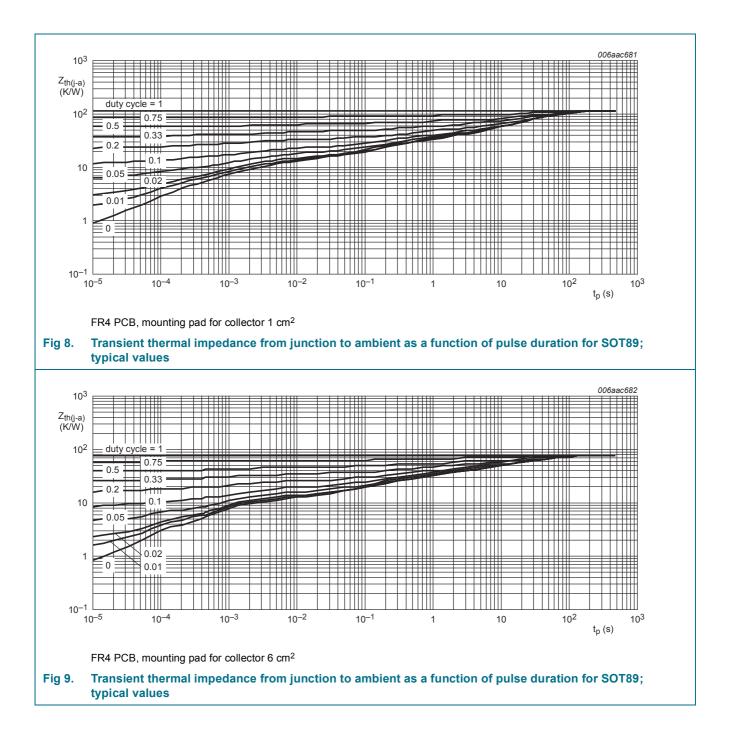
BCP51; BCX51; BC51PA



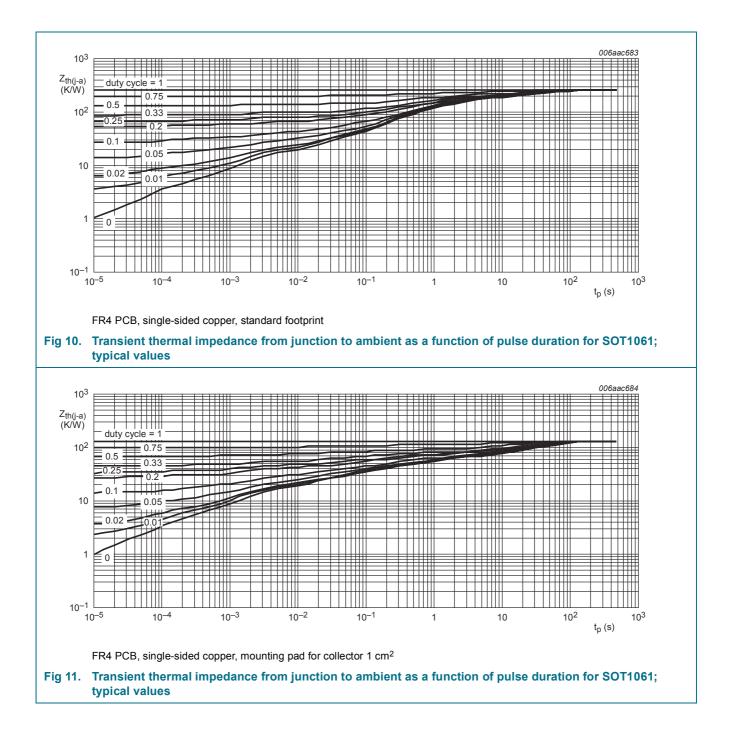
BCP51; BCX51; BC51PA



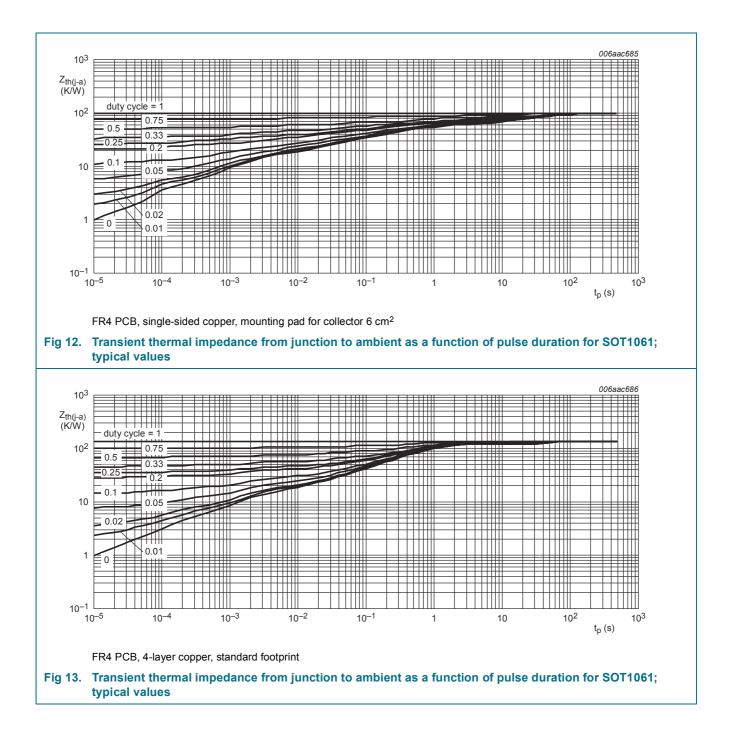
BCP51; BCX51; BC51PA



BCP51; BCX51; BC51PA

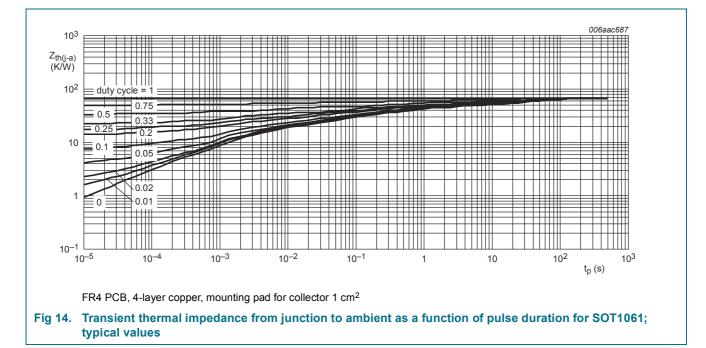


BCP51; BCX51; BC51PA



BCP51; BCX51; BC51PA

45 V, 1 A PNP medium power transistors



7. Characteristics

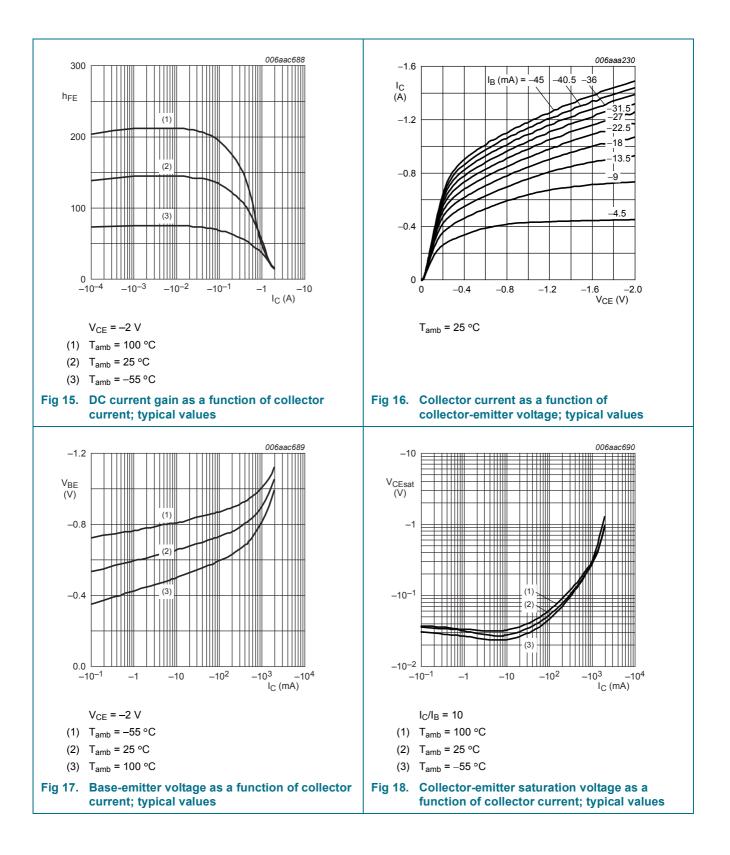
Table 8. Characteristics T = 25 % unlose otherwise

T_{amb} = 25 ℃ unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I _{CBO}	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	cut-off current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C		-	-	-10	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 V; I_C = 0 A$		-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V					
		I _C = –5 mA		63	-	-	
		I _C = –150 mA		63	-	250	
		I _C = –500 mA	[1]	40	-	-	
	DC current gain	V _{CE} = -2 V					
	h _{FE} selection -10	I _C = –150 mA		63	-	160	
	h _{FE} selection -16	I _C = –150 mA		100	-	250	
V _{CEsat}	collector-emitter saturation voltage	I _C = –500 mA; I _B = –50 mA	[1]	-	-	-0.5	V
V _{BE}	base-emitter voltage	V_{CE} = -2 V; I _C = -500 mA	[1]	-	-	-1	V
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz		-	15	-	pF
f _T	transition frequency	V _{CE} = -5 V; I _C = -50 mA; f = 100 MHz		-	145	-	MHz

[1] Pulse test: $t_p \le 300 \ \mu s; \delta = 0.02$.

BCP51; BCX51; BC51PA



BCP51_BCX51_BC51PA

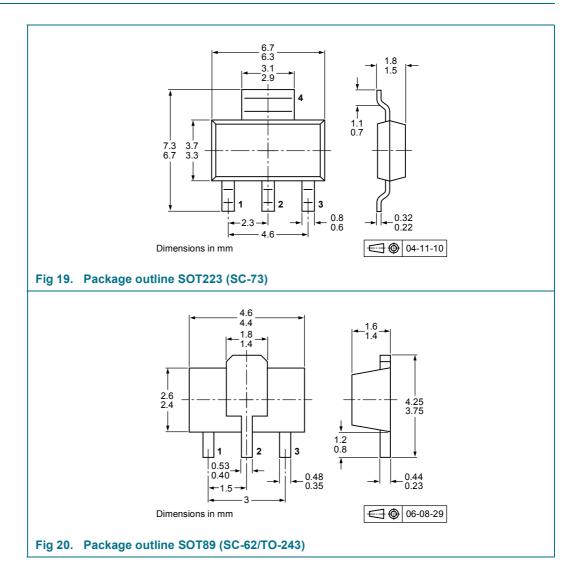
45 V, 1 A PNP medium power transistors

8. Test information

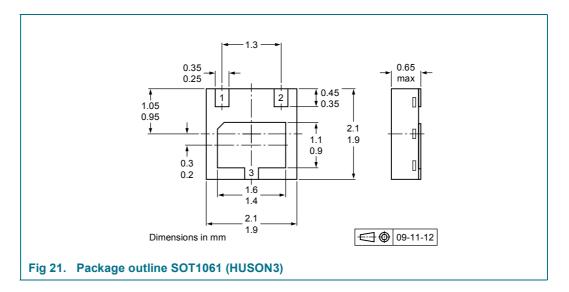
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



45 V, 1 A PNP medium power transistors



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Description	scription		Packing quantity		
number ^[2]				1000	3000	4000	
BCP51	SOT223	8 mm pitch, 12 mm tape and reel		-115	-	-135	
BCX51 SOT89		8 mm pitch, 12 mm tape and reel; T1	[3]	-115	-	-135	
		8 mm pitch, 12 mm tape and reel; T3	[4]	-146	-	-	
BC51PA	SOT1061	4 mm pitch, 8 mm tape and reel		-	-115	-	

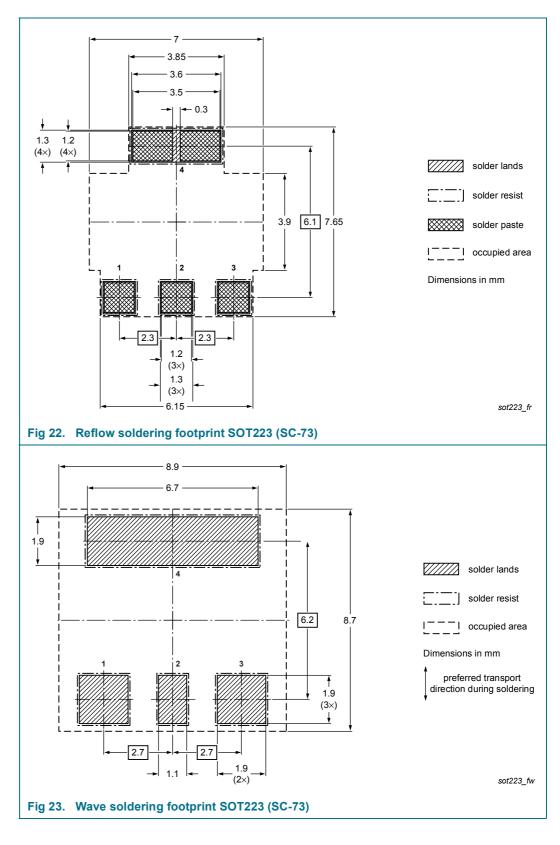
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

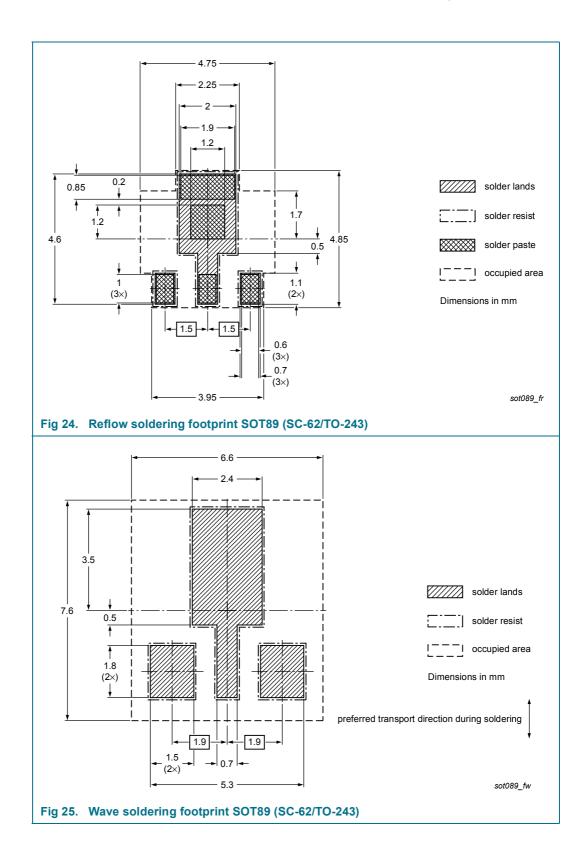
[2] Valid for all available selection groups.

- [3] T1: normal taping
- [4] T3: 90° rotated taping

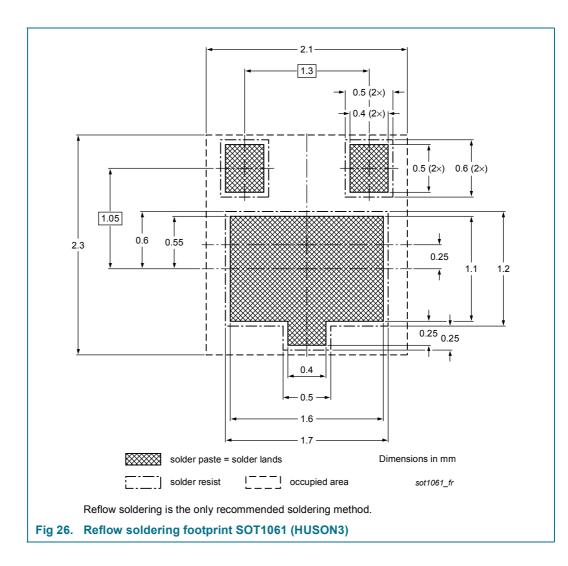
45 V, 1 A PNP medium power transistors

11. Soldering





45 V, 1 A PNP medium power transistors



BCP51_BCX51_BC51PA

45 V, 1 A PNP medium power transistors

12. Revision history

Table 10.Revision history

,				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BCP51_BCX51_BC51PA v.9	20111013	Product data sheet	-	BC636_BCP51_BCX51 v.8
Modifications:	 Deleted typ 	e number BC636		
	 Added Type 	e number BC51PA		
	 Section 1 "I 	Product profile": updated		
	• <u>Table 6</u> and	I <u>7</u> : updated according to la	itest measuremen	ts
	 Figure 1 to 	<u>9, 15, 17, 18</u> and <u>21</u> : upda	ted	
	 Figure 10 to 	o <u>14</u> : added		
	 Section 8 " 	Test information": added		
	 Section 11 	"Soldering": added		
	Section 13	"Legal information": update	d	
BC636_BCP51_BCX51 v.8	20080222	Product data sheet	-	BC636_BCP51_BCX51 v.7
BC636_BCP51_BCX51 v.7	20070629	Product data sheet	-	BC636_BCP51_BCX51 v.6
BC636_BCP51_BCX51 v.6	20060329	Product data sheet	-	BC636_638_640 v.5
				BCP51_52_53 v.5
				BCX51_52_53 v.4
BC636_638_640 v.5	20041011	Product specification	-	BC636_638_640 v.4
BCP51_52_53 v.5	20030206	Product specification	-	BCP51_52_53 v.4
BCX51_52_53 v.4	20011010	Product specification	-	BCX51_52_53 v.3

45 V, 1 A PNP medium power transistors

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

45 V, 1 A PNP medium power transistors

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

14. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

45 V, 1 A PNP medium power transistors

15. Contents

15	Contents
14	Contact information 21
13.4	Trademarks
13.3	Disclaimers
13.2	Definitions 20
13.1	Data sheet status
13	Legal information 20
12	Revision history 19
11	Soldering 16
10	Packing information 15
9	Package outline 14
8.1	Quality information
8	Test information 14
7	Characteristics 12
6	Thermal characteristics
5	Limiting values
•	-
4	Marking
3	Ordering information
2	Pinning information
1.4	Quick reference data
1.2	Applications
1.1	General description
11	•
1	Product profile 1

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2011.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 13 October 2011 Document identifier: BCP51_BCX51_BC51PA